

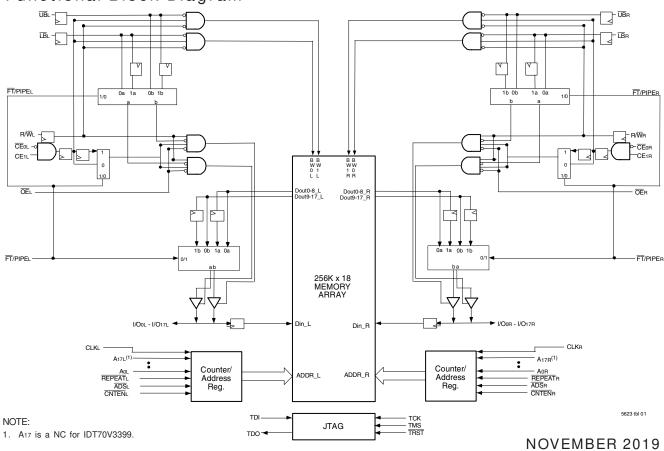
HIGH-SPEED 3.3V 256/128K x 18 SYNCHRONOUS DUAL-PORT STATIC RAM WITH 3.3V OR 2.5V INTERFACE

Features:

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed data access
 - Commercial: 3.6ns (166MHz)/4.2ns (133MHz) (max.)
- Industrial: 4.2ns (133MHz) (max.)
- Selectable Pipelined or Flow-Through output mode
 - Due to limited pin count PL/FT option is not supported on the 128-pin TQFP package. Device is pipelined outputs only on each port.
- Counter enable and repeat features
- Dual chip enables allow for depth expansion without additional logic
- Full synchronous operation on both ports
 - 6ns cycle time, 166MHz operation (6Gbps bandwidth)
 - Fast 3.6ns clock to data out
 - 1.7ns setup to clock and 0.5ns hold on all control, data, and address inputs @ 166MHz
 - Data input, address, byte enable and control registers

- Self-timed write allows fast cycle time
- Separate byte controls for multiplexed bus and bus matching compatibility
- ◆ Dual Cycle Deselect (DCD) for Pipelined Output mode
- LVTTL- compatible, single 3.3V (±150mV) power supply for core
- LVTTL compatible, selectable 3.3V (±150mV) or 2.5V (±100mV) power supply for I/Os and control signals on each port
- Industrial temperature range (-40°C to +85°C) is available at 133MHz.
- Available in a 128-pin Thin Quad Flatpack, 208-pin fine pitch Ball Grid Array, and 256-pin Ball Grid Array
- Supports JTAG features compliant to IEEE 1149.1
 - Due to limited pin count, JTAG is not supported on the 128-pin TQFP package
- Green parts available, see ordering information

Functional Block Diagram



Description:

The IDT70V3319/99 is a high-speed 256/128K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70V3319/99 has been optimized for applications having unidirectional

or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE} 0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode.

The 70V3319/99 can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device (VDD) remains at 3.3V.

Pin Configuration (1,2,3,4,5)

_1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	
I/O ₉ L	NC	Vss	TDO	NC	A _{16L}	A ₁₂ L	AsL	NC	VDD	CLKL	CNTEN 1	A ₄ L	AoL	OPTL	NC	Vss	Α
NC	Vss	NC	TDI	A _{17L} (1)	A13L	A9L	NC	Œ0L	Vss	ADSL	A5L	A ₁ L	Vss	VDDQR	I/O ₈ L	NC	В
VDDQL	I/O _{9R}	VDDQR	PIPE/FTL	NC	A14L	A ₁₀ L	ŪBL	CE ₁ L	Vss	R/WL	A ₆ L	A ₂ L	VDD	I/O8R	NC	Vss	С
NC	Vss	I/O10L	NC	A _{15L}	A ₁₁ L	A7L	ŪB∟	VDD	ŌĒL	REPEAT	_ A3L	VDD	NC	VDDQL	I/O7L	I/O7R	D
I/O _{11L}	NC	VDDQR	I/O10R										I/O ₆ L	NC	Vss	NC	E
VDDQL	I/O11R	NC	Vss										Vss	I/O ₆ R	NC	VDDQR	F
NC	Vss	I/O _{12L}	NC					/3319 F208					NC	VDDQL	I/O ₅ L	NC	G
VDD	NC	VDDQR	I/O12R					G20					VDD	NC	Vss	I/O ₅ R	Н
VDDQL	VDD	Vss	Vss					08-P					Vss	VDD	Vss	VDDQR	J
I/O _{14R}	Vss	I/O13R	Vss					pBG/ o Vie					I/O3R	VDDQL	I/O4R	Vss	K
NC	I/O14L	VDDQR	I/O13L										NC	I/O3L	Vss	I/O4L	L
VDDQL	NC	I/O _{15R}	Vss										Vss	NC	I/O ₂ R	VDDQR	М
NC	Vss	NC	I/O _{15L}										I/O1R	VDDQL	NC	I/O2L	N
I/O _{16R}	I/O16L	VDDQR	NC	TRST	A _{16R}	A ₁₂ R	A ₈ R	NC	VDD	CLKR	ONTEN I	A4R	NC	I/O1L	Vss	NC	Р
Vss	NC	I/O17R	TCK	A _{17R} (1)	A13R	A9R	NC	CE _{0R}	Vss	ĀDSR	A ₅ R	A _{1R}	Vss	VDDQL	I/Oor	VDDQR	R
NC	I/O17L	VDDQL	TMS	NC	A _{14R}	A _{10R}	ŪBR	CE _{1R}	Vss	R/WR	A ₆ R	A ₂ R	Vss	NC	Vss	NC	Т
Vss	NC	PIPE/FT _R	NC	A _{15R}	A _{11R}	A7R	ŪBR	VDD	ŌĒR	REPEAT	r A 3R	Aor	VDD	OPTR	NC	I/OoL	U

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- 1. A₁₇ is a NC for IDT70V3399.
- 2. All VDD pins must be connected to 3.3V power supply.
- 3. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 4. All Vss pins must be connected to ground supply.
- 5. Package body is approximately 15mm x 15mm x 1.4mm with 0.8mm ball pitch.
- $\ensuremath{\mathsf{6}}.$ This package code is used to reference the package diagram.
- 7. This text does not indicate orientation of the actual part-marking.



Pin Configuration $^{(1,2,3,4,5)}$ (con't.)

70V3319/99 BC256⁽⁶⁾ BCG256⁽⁶⁾

256-Pin BGA Top View⁽⁷⁾

A1	A2	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16
NC	TDI	NC	A17L ⁽¹⁾	A 14L	A 11L	A 8L	NC	CE1L	OEL	CNTENL	A 5L	A 2L	A 0L	NC	NC
B1	B2	B3	B4	B5	B6	B7	B8	B9	B10	B11	B12	B13	B14	B15	B16
NC	NC	TDO	NC	A 15L	A 12L	A 9L	UBL	CEol	R/WL	REPEATL	A 4L	A1L	VDD	NC	NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13	C14	C15	C16
NC	I/O9L	Vss	A 16L	A 13L	A10L	A 7L	NC	LBL	CLKL	ADSL	A 6L	A 3L	OPTL	NC	I/O8L
D1	D2	D3	D4	D5	D6	d7	d8	D9	D10	D11	D12	D13	D14	D15	D16
NC	I/O9R	NC	PIPE/FTL	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	VDDQR	Vddqr	VDD	NC	NC	I/O8R
E1	E2	E3	E4	E5	E6	E7	E8	E9	E10	E11	E12	E13	E14	E15	E16
I/O10R	I/O10L	NC	Vddql	Vdd	Vdd	Vss	Vss	Vss	Vss	VDD	VDD	Vddqr	NC	I/O7L	I/O7R
F1	F2	F3	F4	F5	F6	F7	F8	F9	F10	F11	F12	F13	F14	F15	F16
I/O11L	NC	I/O11R	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O6R	NC	I/O6L
G1	G2	G3	G4	G5	G6	G7	G8	G9	G10	G11	G12	G13	G14	G15	G16
NC	NC	I/O12L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	VDDQL	I/O5L	NC	NC
H1	H2	H3	H4	H5	H6	H7	H8	H9	H10	H11	H12	H13	H14	H15	H16
NC	I/O12R	NC	Vddqr	Vss	Vss	V SS	Vss	Vss	Vss	Vss	Vss	Vddql	NC	NC	I/O5R
J1	J2	J3	J4	J5	J6	J7	_{J8}	^{J9}	J10	J11	J12	J13	J14	J15	J16
I/O13L	I/O14R	I/O13R	VDDQL	Vss	Vss	V SS	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O4R	I/ О зп	I/O4L
K1	K2	K3	K4	K5	K6	K7	K8	K9	K10	K11	K12	K13	K14	K15	K16
NC	NC	I/O14L	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	NC	NC	I/O3L
L1	L2	L3	L4	L5	L6	L7	L8	L9	L10	L11	L12	L13	L14	L15	L16
I/O15L	NC	I/O15R	VDDQR	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	VDDQL	I/O2L	NC	I/O2R
M1	M2	M3	m4	M5	M6	M7	M8	M9	M10	M11	M12	M13	M14	M15	M16
I/O16R	I/O16L	NC	Vddqr	Vdd	Vdd	Vss	Vss	Vss	Vss	VDD	Vdd	VDDQL	I/O1R	I/O1L	NC
N1	N2	N3	N4	N5	N6	N7	N8	n9	N10		N12	N13	N14	N15	N16
NC	I/O17R	NC	PIPE/FTR	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr		Vddql	VDD	NC	I/O0R	NC
P1	P2	P3	P4	P5	P6	P7	P8	P9	P10	P11	P12	P13	P14	P15	P16
NC	I/O17L	TMS	A 16R	A 13R	A 10R	A 7R	NC	LBr	CLKR	ADSR	A 6R	A 3R	NC	NC	I/OoL
R1	R2	R3	R4	R5	R6	R7	R8	R9	R10	R11	R12	R13	R14	R15	R16
NC	NC	TRST	NC	A 15R	A 12R	A 9R	UBr	CE0R	R/WR	REPEATR	A 4R	A 1R	OPTR	NC	NC
T1	T2	T3	T4	T5	T6	T7	T8	T9	T10	T11	T12	T13	T14	T15	T16
NC	TCK	NC	A 17R ⁽¹⁾	A 14R	A 11R	A 8R	NC	CE1R	OEr	CNTENR	A 5R	A 2R	A 0R	NC	NC

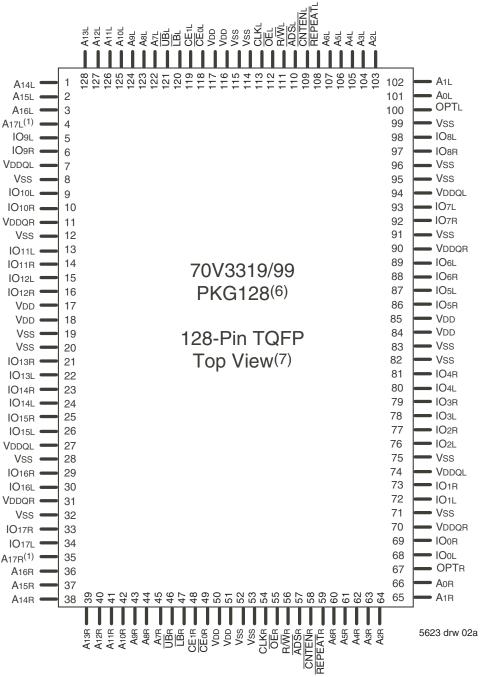
5623 drw 02d

- 1. A₁₇ is a NC for IDT70V3399.
- 2. All VDD pins must be connected to 3.3V power supply.
- 3. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 4. All Vss pins must be connected to ground supply.
- 5. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.
- 6. This package code is used to reference the package diagram.
- 7. This text does not indicate orientation of the actual part-marking.



Industrial and Commercial Temperature Range

Pin Configuration^(1,2,3,4,5,8,9) (con't.)



- 1. A₁₇ is a NC for IDT70V3399.
- 2. All VDD pins must be connected to 3.3V power supply.
- 3. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 4. All Vss pins must be connected to ground supply.
- 5. Package body is approximately 14mm x 20mm x 1.4mm.
- 6. This package code is used to reference the package diagram.
- 7. This text does not indicate orientation of the actual part-marking.
- 8. PIPE/FT option in PKG128 is not supported due to limitation in pin count. Device is pipelined outputs only on each port.
- 9. Due to the limited pin count, JTAG is not supported in the PKG128 package.

High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Pin Names

Left Port	Right Port	Names				
CEOL, CE1L	CEOR, CE1R	Chip Enables ⁽⁶⁾				
R/WL	R/WR	Read/Write Enable				
ŌĒL	ŌĒR	Output Enable				
A0L - A17L ⁽¹⁾	A0R - A17R ⁽¹⁾	Address				
I/O0L - I/O17L	I/O0R - I/O17R	Data Input/Output				
CLKL	CLKR	Clock				
PIPE/FT _L (5)	PIPE/FT _R ⁽⁵⁾	Pipeline/Flow-Through				
ĀDS∟	ĀDS _R	Address Strobe Enable				
CNTENL	<u>CNTEN</u> R	Counter Enable				
REPEATL	REPEAT _R	Counter Repeat ⁽⁴⁾				
ŪB∟	ŪB⊓	Upper Byte Enable (I/O9-I/O17) ⁽⁶⁾				
LB L	LB R	Lower Byte Enable (I/Oo-I/O8) ⁽⁶⁾				
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽²⁾				
OPTL	OPTR	Option for selecting VDDQx ^(2,3)				
V	DD	Power (3.3V) ⁽²⁾				
V	ss	Ground (0V)				
Т	DI	Test Data Input				
П	00	Test Data Output				
T	CK	Test Logic Clock (10MHz)				
T	MS	Test Mode Select				
TF	RST	Reset (Initialize TAP Controller)				

- 1. A₁₇ is a NC for IDT70V3399.
- VDD, OPTx, and VDDQx must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 3. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VIH (3.3V), then that port's I/Os and controls will operate at 3.3V levels and VDDQX must be supplied at 3.3V. If OPTx is set to VIL (0V), then that port's I/Os and address controls will operate at 2.5V levels and VDDQX must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.
- When REPEATx is asserted, the counter will reset to the last valid address loaded via ADSx.
- PIPE/FT option in PK-128 package is not supported due to limitation in pin count.
 Device is pipelined output mode only on each port.
- 6. Chip Enables and Byte Enables are double buffered when $PL/\overline{FT} = V_{IH}$, i.e., the signals take two cycles to deselect.



High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAN

Industrial and Commercial Temperature Range

5623 tbl 02

Truth Table I—Read/Write and Enable Control(1,2,3)

ŌĒ	CLK	Œ	CE ₁	ŪB	ĪΒ	R/ W	Upper Byte I/O9-17	Lower Byte I/O ₀₋₈	MODE
Х	1	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected-Power Down
Х	1	Х	L	Х	Х	Х	High-Z	High-Z	Deselected-Power Down
Х	1	L	Н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	1	L	Н	Н	L	L	High-Z	Din	Write to Lower Byte Only
Х	1	L	Н	L	Н	L	Din	High-Z	Write to Upper Byte Only
Х	1	L	Н	L	L	L	Din	Din	Write to Both Bytes
L	1	L	Н	Н	L	Н	High-Z	D оит	Read Lower Byte Only
L	1	L	Н	L	Н	Н	D ouт	High-Z	Read Upper Byte Only
L	1	L	Н	L	L	Н	Dout	D оит	Read Both Bytes
Н	1	L	Н	L	L	Х	High-Z	High-Z	Outputs Disabled

NOTES:

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. \overline{ADS} , \overline{CNTEN} , $\overline{REPEAT} = X$.
- 3. $\overline{\mathsf{OE}}$ is an asynchronous input signal.

Truth Table II—Address Counter Control^(1,2)

	1 4010		J. J			01 001		
External Address	Previous Internal Address	Internal Address Used	CLK	ĀDS	CNTEN	REPEAT ⁽⁶⁾	I/O ⁽³⁾	MODE
Х	Х	An	1	Х	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to last valid ADS load
An	х	An	1	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
An	Ар	Ар	1	Ι	н	Н	Dvo(p)	External Address Blocked—Counter disabled (Ap reused)
Х	Ар	Ap + 1	1	Н	L ⁽⁵⁾	Н	Dvo(p+1)	Counter Enabled—Internal Address generation

NOTES: 5623 tbl 03

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. Read and write operations are controlled by the appropriate setting of R \overline{W} , \overline{CE}_0 , CE1, \overline{UB} , \overline{LB} and \overline{OE} .
- 3. Outputs configured in flow-through output mode: if outputs are in pipelined mode the date out will be delayed by one cycle.
- 4. \overline{ADS} and \overline{REPEAT} are independent of all other memory control signals including \overline{CE}_0 , CE_1 and \overline{UB} , \overline{LB} .
- 5. The address counter advances if $\overline{\text{CNTEN}} = \text{VIL}$ on the rising edge of CLK, regardless of all other memory control signals including $\overline{\text{CE}}_0$, CE_1 , $\overline{\text{UB}}$, $\overline{\text{LB}}$.
- 6. When REPEAT is asserted, the counter will reset to the last valid address loaded via ADS. This value is not set at power-up: a known location should be loaded via ADS during initialization if desired. Any subsequent ADS access during operations will update the REPEAT address location.



Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	VDD
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 150mV
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 150mV

NOTES:

5623 tbl 04

1. This is the parameter TA. This is the "instant on" case temperature.

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	٧
TBIAS ⁽³⁾	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
Тли	Junction Temperature	+150	°C
Іоит	DC Output Current	50	mA

NOTES:

5623 tbl 06

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed VDD + 150mV for more than 25% of the cycle time or 4ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ VDD + 150mV.
- 3. Ambient Temperature Under Bias. No AC Conditions. Chip Deselected.

Recommended DC Operating Conditions with VDDQ at 2.5V

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Core Supply Voltage	3.15	3.3	3.45	٧
VDDQ	I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	٧
Vss	Ground	0	0	0	٧
VIH	Input High Voltage (Address & Control Inputs)	1.7		VDDQ + 100mV ⁽²⁾	٧
VIH	Input High Voltage - I/O ⁽³⁾	1.7		VDDQ + 100mV ⁽²⁾	٧
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.7	٧

NOTES

5623 tb I 05a

- 1. Undershoot of $V_{IL \ge} -1.5V$ for pulse width less than 10ns is allowed.
- 2. VTERM must not exceed VDDQ + 100mV.
- To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIL (0V), and VDDOX for that port must be supplied as indicated above.

Recommended DC Operating Conditions with VDDQ at 3.3V

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Core Supply Voltage	3.15	3.3	3.45	٧
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	٧
Vss	Ground	0	0	0	٧
VIН	Input High Voltage (Address & Control Inputs) ⁽³⁾	2.0		VDDQ + 150mV ⁽²⁾	V
V⊪	Input High Voltage - I/O(3)	2.0		VDDQ + 150mV ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	٧

NOTES:

5623 tbl 05b

- 1. Undershoot of VIL $_{\geq}$ -1.5V for pulse width less than 10ns is allowed.
- 2. VTERM must not exceed VDDQ + 150mV.
- To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to ViH (3.3V), and VDDOX for that port must be supplied as indicated above.

Capacitance⁽¹⁾(TA = +25°C, F = 1.0MHz)

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	8	pF
Соит ⁽³⁾	Output Capacitance	Vout = 3dV	10.5	pF

5623 tbl 07

NOTES:

- 1. These parameters are determined by device characterization, but are not production tested.
- 2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($VDD = 3.3V \pm 150 mV$)

			70V33	70V3319/99S	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	VDDQ = Max., VIN = 0V to VDDQ	_	10	μΑ
llo	Output Leakage Currentt ⁽¹⁾	$\overline{\overline{\text{CE}}}_0 = \text{ViH or CE1} = \text{ViL}, \text{ Vout} = 0 \text{V to VDDQ}$		10	μΑ
Vol (3.3V)	Output Low Voltage ⁽²⁾	lol = +4mA, VDDQ = Min.		0.4	V
Vон (3.3V)	Output High Voltage ⁽²⁾	IOH = -4mA, VDDQ = Min.	2.4	_	V
Vol (2.5V)	Output Low Voltage ⁽²⁾	IOL = +2mA, VDDQ = Min.	_	0.4	٧
Voн (2.5V)	Output High Voltage ⁽²⁾	IOH = -2mA, VDDQ = Min.	2.0	_	٧

NOTE:

1. At $VDD \le 2.0V$ leakages are undefined.

2. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.5 for details.

5623 tbl 08



DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ (VDD = 3.3V ± 150mV)

<u> </u>	 	supply vollage trainge (vi	00 - 0.	<u> </u>		··· • <i>/</i>			
						9/99S166 Only			
Symbol	Parameter	Test Condition	Versio	n	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
IDD	Dynamic Operating	CEL and CER= VIL,	COM'L	S	370	500	320	400	mA
	Current (Both Ports Active)	Outputs Disabled, $f = fMAX^{(1)}$	IND	S		_	320	480	
ISB1	Standby Current	CEL = CER = VIH,	COM'L	S	125	200	115	160	mA
	(Both Ports - TTL Level Inputs)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	S			115	195	
ISB2	Standby Current	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽⁵⁾	COM'L	S	250	350	220	290	mA
	(One Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S			220	350	
ISB3	Full Standby Current (Both Ports - CMOS	Both Ports Outputs Disabled CEL and CER ≥ VDDQ - 0.2V,	COM'L	S	15	30	15	30	mA
	Level Inputs)	$ \begin{array}{l} \text{VIN} \geq \text{VDDQ} - 0.2\text{V} \\ \text{or VIN} \leq 0.2\text{V}, \ f = 0^{(2)} \end{array} $	IND	s			15	40	
ISB4	Full Standby Current	\overline{CE} "A" $\leq 0.2V$ and \overline{CE} "B" $\geq V$ DDQ - $0.2V^{(5)}$	COM'L	S	250	350	220	290	mA
	(One Port - CMOS Level Inputs)	$VIN \ge VDDQ - 0.2V$ or $VIN \le 0.2V$ Active Port, Outputs Disabled, $f = fMAX^{(1)}$	IND	S			220	350	

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 3.3V, $TA = 25^{\circ}C$ for Typ, and are not production tested. IDD DC(f=0) = 120mA (Typ).
- 5. $\overline{CE}x = V_{IL} \text{ means } \overline{CE}_{0X} = V_{IL} \text{ and } CE_{1X} = V_{IH}$
 - $\overline{CE}x = VIH \text{ means } \overline{CE}0x = VIH \text{ or } CE1x = VIL$

 - $\begin{array}{l} \overline{CEx} \leq \text{Virial fields} & \overline{CEox} = \text{Virial field} & \overline{CEox} \leq 0.2 \text{V} \text{ and } \overline{CEix} \geq \text{VDDQ} 0.2 \text{V} \\ \overline{CEx} \geq \text{VDDQ} 0.2 \text{V} \text{ means } \overline{\overline{CEox}} \geq \text{VDDQ} 0.2 \text{V} \text{ or } \overline{CEix} 0.2 \text{V} \\ \end{array}$
 - "X" represents "L" for left port or "R" for right port.

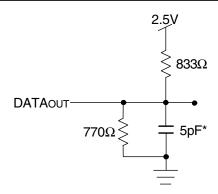


70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM Industrial and Commercial Temperature Range

AC Test Conditions (VDDQ - 3.3V/2.5V)

710 TOOL OUTSTITUTE	V D D Q 0.0 V / L.0 V /
Input Pulse Levels (Address & Controls)	GND to 3.0V/GND to 2.4V
Input Pulse Levels (I/Os)	GND to 3.0V/GND to 2.4V
Input Rise/Fall Times	2ns
Input Timing Reference Levels	1.5V/1.25V
Output Reference Levels	1.5V/1.25V
Output Load	Figures 1 and 2

5623 tbl 10



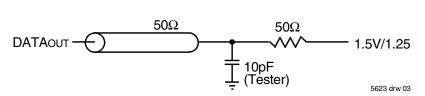


Figure 1. AC Output Test load.

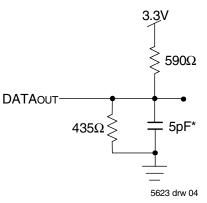


Figure 2. Output Test Load (For tckLz, tckHz, toLz, and toHz).
*Including scope and jig.

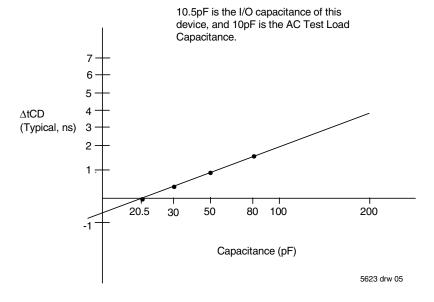


Figure 3. Typical Output Derating (Lumped Capacitive Load).



70V3319/99S
High-Speed 3 3V 256/128K v. 18 Dual-Port Synchronous Static RAN

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(2,3)}$ (VDD = 3.3V ± 150mV, TA = 0°C to +70°C)

		70V3319 Com'	TA = 0°C to 70V3319/99S166 Com'l Only		70V3319/99S133 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽¹⁾	20		25		ns
tCYC2	Clock Cycle Time (Pipelined) ⁽¹⁾	6		7.5		ns
tcH1	Clock High Time (Flow-Through) ⁽¹⁾	6		7		ns
tCL1	Clock Low Time (Flow-Through) ⁽¹⁾	6		7		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	2.1		2.6		ns
tCL2	Clock Low Time (Pipelined) ⁽¹⁾	2.1		2.6		ns
tsa	Address Setup Time	1.7		1.8		ns
tha	Address Hold Time	0.5		0.5		ns
tsc	Chip Enable Setup Time	1.7		1.8		ns
tHC	Chip Enable Hold Time	0.5		0.5		ns
tsB	Byte Enable Setup Time	1.7		1.8	_	ns
tнв	Byte Enable Hold Time	0.5		0.5		ns
tsw	R/W Setup Time	1.7		1.8	_	ns
tHW	R/W Hold Time	0.5		0.5	_	ns
tsp	Input Data Setup Time	1.7		1.8	_	ns
tHD	Input Data Hold Time	0.5		0.5	_	ns
tsad	ADS Setup Time	1.7		1.8	_	ns
thad	ADS Hold Time	0.5		0.5		ns
tscn	CNTEN Setup Time	1.7		1.8		ns
thcn	CNTEN Hold Time	0.5		0.5		ns
tsrpt	REPEAT Setup Time	1.7		1.8		ns
thrpt	REPEAT Hold Time	0.5		0.5		ns
toe	Output Enable to Data Valid	_	4.0		4.2	ns
toLZ	Output Enable to Output Low-Z	1		1		ns
tonz	Output Enable to Output High-Z	1	3.6	1	4.2	ns
tCD1	Clock to Data Valid (Flow-Through)(1)	_	12		15	ns
tCD2	Clock to Data Valid (Pipelined) ⁽¹⁾		3.6		4.2	ns
toc	Data Output Hold After Clock High	1		1		ns
tckhz	Clock High to Output High-Z	1	3	1	3	ns
tcklz	Clock High to Output Low-Z	1		1	_	ns
Port-to-Port D	· lelay	•		•	•	
tco	Clock-to-Clock Offset	5		6		ns
				•		

NOTES

5623 tbl 11

^{1.} The Pipelined output parameters (tcyc2, tcb2) apply to either or both left and right ports when $\overline{FT}/PIPEx = VIH$. Flow-through parameters (tcyc1, tcb1) apply when $\overline{FT}/PIPE = VIL$ for that port.

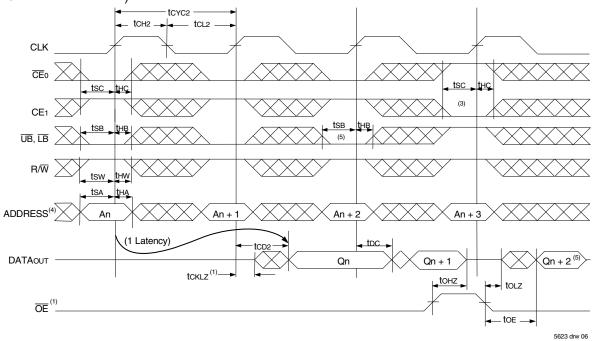
^{2.} All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (\overline{OE}) and $\overline{FT}/PIPE$. $\overline{FT}/PIPE$ should be treated as a DC signal, i.e. steady state during operation.

^{3.} These values are valid for either level of VDDQ (3.3V/2.5V). See page 5 for details on selecting the desired operating voltage levels for each port.

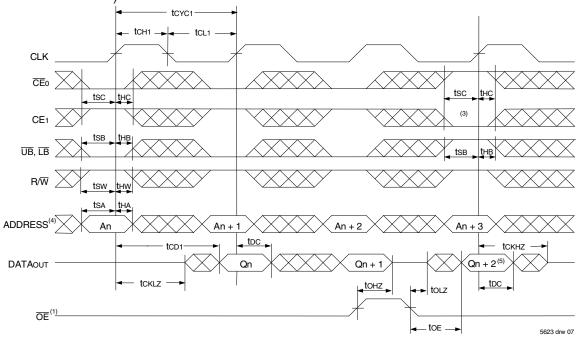


High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAM

Timing Waveform of Read Cycle for Pipelined Operation $(\overline{\textbf{FT}}/\text{PIPE}'x' = VIH)^{(2)}$



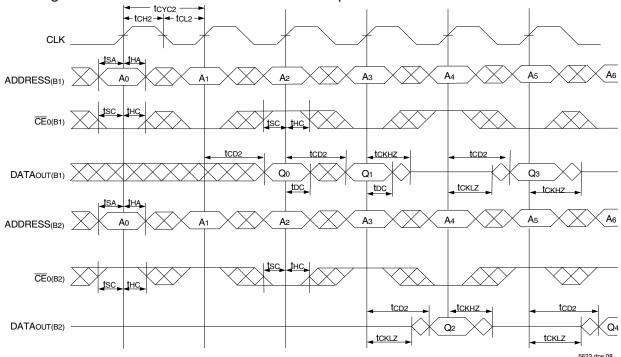
Timing Waveform of Read Cycle for Flow-through Output $(\overline{FT}/PIPE"x" = VIL)^{(2,6)}$



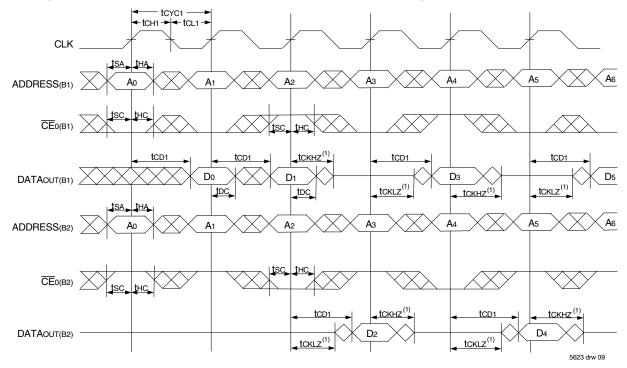
- 1. $\overline{\text{OE}}$ is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 2. $\overline{ADS} = V_{IL}$, \overline{CNTEN} and $\overline{REPEAT} = V_{IH}$.
- 3. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$, $CE_1 = V_{IL}$, \overline{UB} , $\overline{LB} = V_{IH}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If $\overline{\sf UB}$, $\overline{\sf LB}$ was HIGH, then the appropriate Byte of DATAouT for Qn + 2 would be disabled (High-Impedance state).
- 6. "x" denotes Left or Right port. The diagram is with respect to that port.



Timing Waveform of a Multi-Device Pipelined Read^(1,2)



Timing Waveform of a Multi-Device Flow-Through $Read^{(1,2)}$



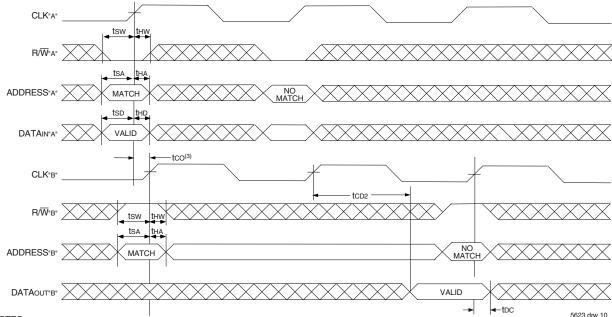
- B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70V3319/99 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{UB}}$, $\overline{\text{LB}}$, $\overline{\text{OE}}$, and $\overline{\text{ADS}}$ = VIL; CE_{1(B1)}, CE_{1(B2)}, R/ $\overline{\text{W}}$, $\overline{\text{CNTEN}}$, and $\overline{\text{REPEAT}}$ = VIH.



70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RAI

Industrial and Commercial Temperature Rang

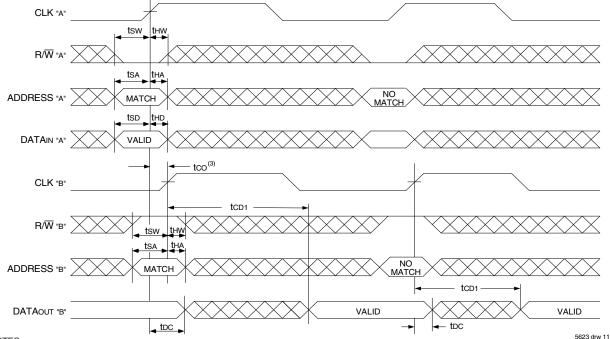
Timing Waveform of Left Port Write to Pipelined Right Port Read (1,2,4)



NOTES:

- 1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{REPEAT} = VIH.
- 2. $\overline{OE} = V_{IL}$ for Port "B", which is being read from. $\overline{OE} = V_{IH}$ for Port "A", which is being written to.
- 3. If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcvc² + tcp²). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + tcvc² + tcp²).
- 4. All timing is the same for Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite of Port "A"

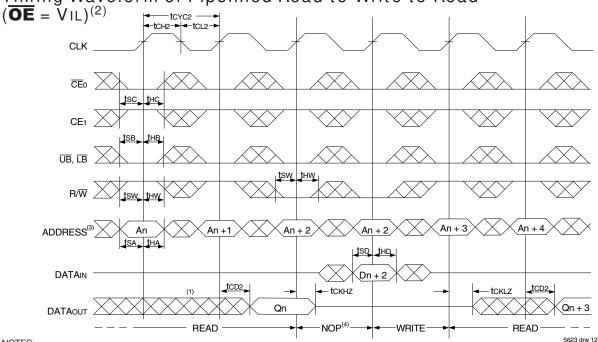
Timing Waveform with Port-to-Port Flow-Through Read (1,2,4)



- 1. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{REPEAT} = VIH.
- 2. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 3. If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcyc + tcpi). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcpi).
- 4. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".



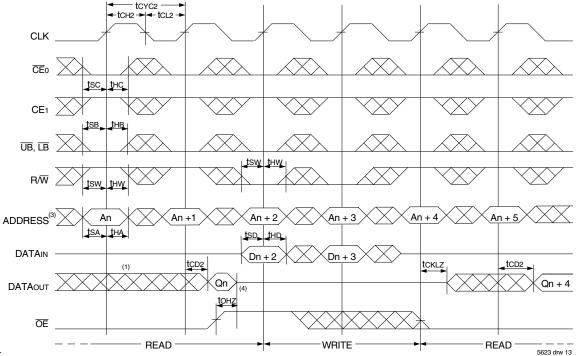
Timing Waveform of Pipelined Read-to-Write-to-Read



NOTES:

- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- \overline{CE}_0 , \overline{UB} , \overline{LB} , and $\overline{ADS} = VIL$; \overline{CE}_1 , \overline{CNTEN} , and $\overline{REPEAT} = VIH$. "NOP" is "No Operation".
- Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.

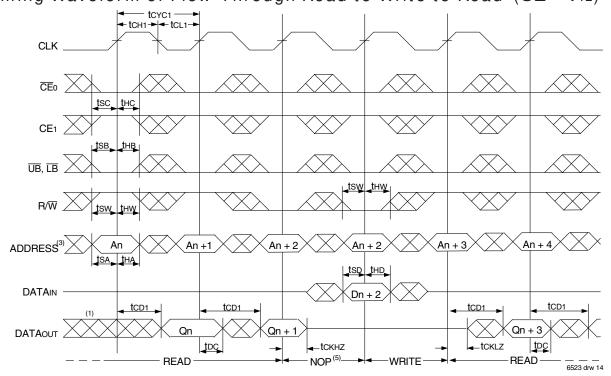
Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)(2)



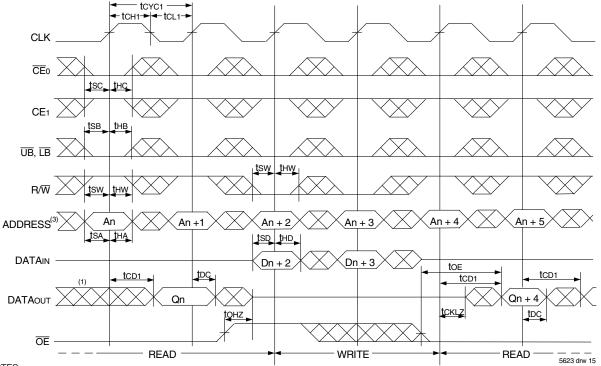
- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1, \overline{CNTEN} , and \overline{REPEAT} = VIH.
- 3. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK; numbers are for reference
- 4. This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.



Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** = VIL)⁽²⁾



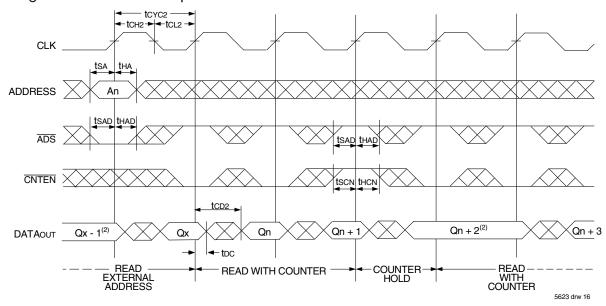
Timing Waveform of Flow -Through Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



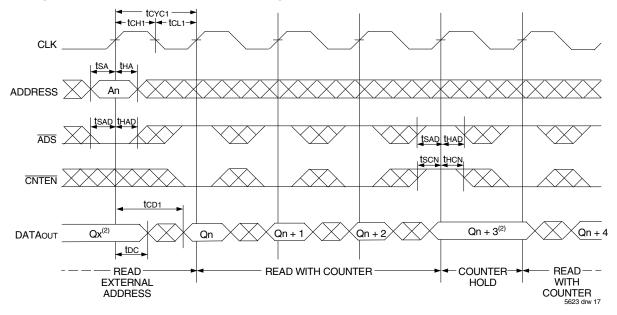
- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; $\overline{CE_1}$, \overline{CNTEN} , and \overline{REPEAT} = VIH.
- 3. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.



Timing Waveform of Pipelined Read with Address Counter Advance(1)



Timing Waveform of Flow -Through Read with Address Counter Advance $^{(1)}$

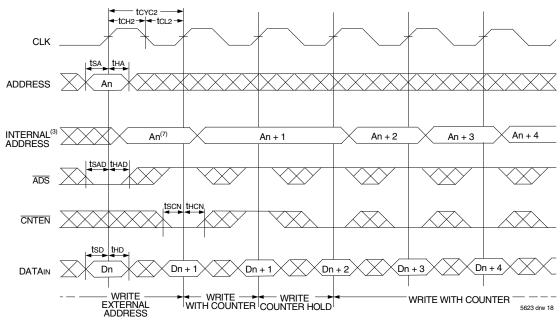


- 1. \overline{CE}_0 , \overline{OE} , \overline{UB} , \overline{LB} = VIL; CE1, R/ \overline{W} , and \overline{REPEAT} = VIH.
- 2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.

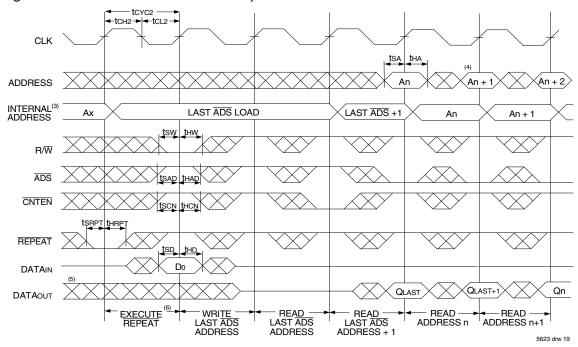


70V3319/99S High-Speed 3 3V 256/128K x 18 Dual-Port Synchronous Static RAN

Timing Waveform of Write with Address Counter Advance (Flow-through or Pipelined Inputs)⁽¹⁾



Timing Waveform of Counter Repeat (2)



- 1. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{REPEAT} = V_{IH}$.
- 2. \overline{CE}_0 , \overline{UB} , \overline{LB} = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or $\underline{\text{High-impe}}$ dance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during REPEAT operation. A READ or WRITE cycle may be coincidental with the counter REPEAT cycle: Address loaded by last valid ADS load will be accessed. Extra cycles are shown here simply for clarification. For more information on REPEAT function refer to Truth Table II.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.



70V3319/99S High-Speed 3.3V 256/128K x 18 Dual-Port Synchronous Static RA

Functional Description

The IDT70V3319/99 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

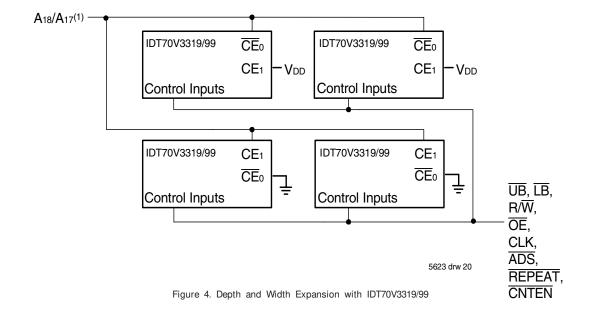
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on $\overline{\text{CE}}$ oor a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V3319/99s for depth expansion configurations. Two cycles are required with $\overline{\text{CE}}$ 0 LOW and CE1 HIGH to reactivate the outputs.

Depth and Width Expansion

The IDT70V3319/99 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

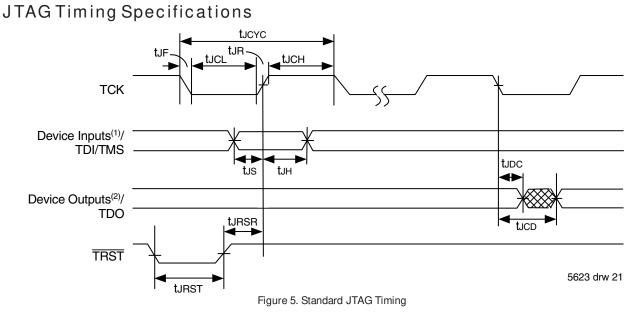
The IDT70V3319/99 can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 36-bits or wider.



NOTE:

1. A₁₇ is for IDT70V3319, A₁₆ is for IDT70V3399.

mg. opcou die v zooi zon n no zam v ent eyne



NOTES:

- 1. Device inputs = All device inputs except TDI, TMS, and TRST.
- 2. Device outputs = All device outputs except TDO.

JTAG AC Electrical Characteristics (1,2,3,4)

		70V3319/99		9
Symbol	Parameter	Min.	Max.	Units
tucyc	JTAG Clock Input Period	100	_	ns
tлсн	JTAG Clock HIGH	40	_	ns
tucı	JTAG Clock Low	40	_	ns
tur	JTAG Clock Rise Time		3 ⁽¹⁾	ns
tur	JTAG Clock Fall Time		3 ⁽¹⁾	ns
turst	JTAG Reset	50	_	ns
tursr	JTAG Reset Recovery	50	_	ns
tuco	JTAG Data Output		25	ns
tudo	JTAG Data Output Hold	0		ns
tus	JTAG Setup	15		ns
tлн	JTAG Hold	15	_	ns

NOTES:

5623 tbl 12

- 1. Guaranteed by design.
- 2. 30pF loading on external output signals.
- 3. Refer to AC Electrical Test Conditions stated earlier in this document.
- JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.



70V3319/99S High-Speed 3 3V 256/128K v 18 Dual-Port Synchronous Static RAN

Industrial and Commercial Temperature Range

Identification Register Definitions

Instruction Field	Value	Description	
Revision Number (31:28)	0x0	Reserved for version number	
IDT Device ID (27:12)	0x0314 ⁽¹⁾	Defines IDT part number	
IDT JEDEC ID (11:1)	0x33	Allows unique identification of device vendor as IDT	
ID Register Indicator Bit (Bit 0)	1	Indicates the presence of an ID register	

NOTE:

5623 tbl 13

5623 tbl 15

Scan Register Sizes

Register Name	Bit Size	
Instruction (IR)	4	
Bypass (BYR)	1	
Identification (IDR)	32	
Boundary Scan (BSR)	Note (3)	

5623 tbl 14

System Interface Parameters

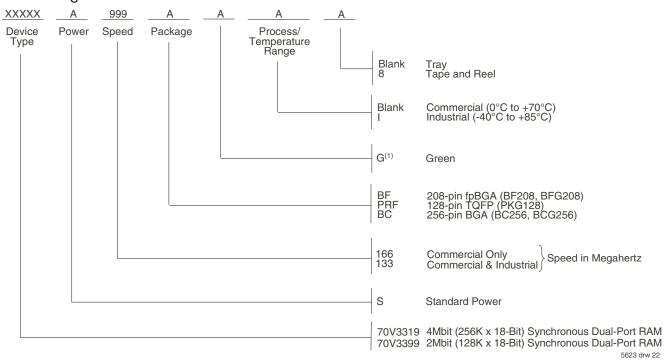
Instruction	Code	Description
EXTEST	0000	Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.
BYPASS	1111	Places the bypass register (BYR) between TDI and TDO.
IDCODE	0010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.
HIGHZ	0011	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers to a High-Z state.
SAMPLE/PRELOAD	0001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ² to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.
RESERVED	All other codes	Several combinations are reserved. Do not use codes other than those identified above.

- 1. Device outputs = All device outputs except TDO.
- 2. Device inputs = All device inputs except TDI, TMS, and $\overline{\mbox{TRST}}.$
- 3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.

^{1.} Device ID for IDT70V3399 is 0x0315.



Ordering Information



NOTES:

1. Contact your local sales office for industrial temp. range for other speeds, packages and powers. LEAD FINISH (SnPb) parts are Obsolete excluding BGA & fpBGA. Product Discontinuation Notice - PDN# SP-17-02 Note that information regarding recently obsoleted parts is included in this datasheet for customer convenience.

Orderable Part Information

Speed (MHz)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
133	70V3319S133BC	BC256	CABGA	С
	70V3319S133BC8	BC256	CABGA	С
	70V3319S133BCGI	BCG256	CABGA	1
	70V3319S133BCI	BC256	CABGA	- 1
	70V3319S133BCl8	BC256	CABGA	1
	70V3319S133BF	BF208	CABGA	С
	70V3319S133BF8	BF208	CABGA	С
	70V3319S133BFI	BF208	CABGA	1
	70V3319S133BFI8	BF208	CABGA	1
	70V3319S133PRFGI	PKG128	TQFP	1
	70V3319S133PRFGI8	PKG128	TQFP	I
166	70V3319S166BC	BC256	CABGA	С
	70V3319S166BC8	BC256	CABGA	С
	70V3319S166BCG	BCG256	CABGA	С
	70V3319S166BF	BF208	CABGA	С
	70V3319S166BF8	BF208	CABGA	С
	70V3319S166BFG	BFG208	CABGA	С
	70V3319S166BFG8	BFG208	CABGA	С
	70V3319S166PRFG	PKG128	TQFP	С
	70V3319S166PRFG8	PKG128	TQFP	С

Speed (MHz)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
133	70V3399S133BC	BC256	CABGA	С
	70V3399S133BC8	BC256	CABGA	С
	70V3399S133BCI	BC256	CABGA	I
	70V3399S133BCl8	BC256	CABGA	I
	70V3399S133BF	BF208	CABGA	С
	70V3399S133BF8	BF208	CABGA	С
	70V3399S133BFI	BF208	CABGA	I
	70V3399S133BFI8	BF208	CABGA	I
166	70V3399S166BC	BC256	CABGA	С
	70V3399S166BC8	BC256	CABGA	С
	70V3399S166BF	BF208	CABGA	С
	70V3399S166BF8	BF208	CABGA	С
	70V3399S166BFG	BFG208	CABGA	С
	70V3399S166BFG8	BFG208	CABGA	С

Datasheet Document History:

06/02/00: Initial Public Offering

07/12/00: Page 1 Added mux to functional block diagram
06/20/01: Page 1 Added JTAG information for TQFP package

Page 4 Corrected TQFP package size

07/30/01: Page 1 Added PL/FToption

Page 20 Changed maximum value for JTAG AC Electrical Characteristics for tJCD from 20ns to 25ns

Page 9 Added Industrial Temperature DC Parameters

11/20/01: Page 2, 3 & 4 Added date revision for pin configurations

Page 11 Changed to Evalue in AC Electrical Characteristics, please refer to Errata #SMEN-01-05

Page 1 & 22 Replaced TM logo with ® logo

Page 10 Changed AC Test Conditions Input Rise/Fall Times

08/06/02: Consolidated multiple devices into one datasheet

Page 1 & 5 Added DCD capability for Pipelined Outputs

Page 7 Clarified TBIAS and added TJN Page 9 Changed DC Electrical Parameters

Page 11 Removed Clock Rise & Fall Time from AC Electrical Characteristics Table

Removed Preliminary status

05/19/03: Page 11 Added Byte Enable SetupTime & Byte Enable Hold Time to AC Electrical Characteristics Table

Page 22 Added IDT Clock Solution Table

02/08/06: Page 1 Added green availability to features

Page 6 Changed footnote 2 for Truth Table I from ADS, CNTEN, REPEAT = VIH to ADS, CNTEN, REPEAT = X

Page 22 Added green indicator to ordering information

07/25/08: Page 9 Corrected a typo in the DC Chars table
01/19/09: Page 22 Removed "IDT" from orderable part number
10/03/14: Page 22 Added Tape & Reel to the Ordering Information
06/20/18: Product Discontinuation Notice - PDN# SP-17-02

Last time buy expires June 15, 2018

09/12/19: Page 2, 3 & 4 Updated package codes

Page 22 Added Orderable Part Information table and removed IDT Clock Solution table

11/04/19: Page 22 Corrected "ns" to "MHz" in the header of the Orderable Part Information tables

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